

# MSE 460: Electronic Materials, Devices, and Processing

## Lecture 1: Introduction and Orientation

*Qing Cao-University of Illinois at Urbana-Champaign*

*Department of Materials Science and Engineering*

*Department of Chemistry*

*Department of Electrical and Computer Engineering*

*Frederick Seitz Materials Research Laboratory*



# Self-Introduction



2004-2009



2009-2018



Research Interest:

Electronic Materials

Unconventional Electronic Devices

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Office: MRL 1008

Office hour: Friday 2-3 pm



# Targets of MSE 460

- 1) Understand the processing technologies for electronic materials.
- 2) Understand the operational mechanism of various devices,
- 3) Understand the correlation between material properties and device performances,
- 4) Develop the technical insight into the choice of the most appropriate materials and processing techniques for different applications, and obtain of grasp of the most important challenges.



***Engineering is the art of intelligent compromise.***

# About MSE 460 What will be covered in this class?

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## Overview and fundamentals of electronic materials

**Lecture 1: Introduction and Orientation**

**Lecture 2: Overview of Electronic Materials**

**Lecture 3: Free electron Fermi gas**

**Lecture 4: Energy bands**

**Lecture 5: Carrier Concentration in Semiconductors**

**Lecture 6: Shallow dopants and Deep-level traps**

**Lecture 7: Silicon Materials**

**Lecture 8: Oxidation**

**Lecture 9: Doping**

**Lecture 10: Drift and diffusion**

**Lecture 11: Generation and recombination**

# About MSE 460

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## **p-n junctions: Physics and fabrication**

**Lecture 12: Electrostatics of p-n junctions (I)**

**Lecture 13: Electrostatics of p-n junctions (II)**

**Lecture 14: Current Voltage Characteristics of p-n Junctions**

**Lecture 15: Metal Semiconductor interface and Schottky Diode**

**Lecture 16: Lithography I: Basics and Photoresist Chemistry**

**Lecture 17: Lithography II: EUV and Novel Patterning Techniques**

**Lecture 18: Etching Overview**

**Lecture 19: Wet Etching**

**Lecture 20: Dry Etching**

# About MSE 460

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## **p-n junctions: LEDs and solar cells**

**Lecture 22: Light Emitting Diodes**

**Lecture 23: LED Materials**

**Lecture 24: Physics of Solar Cells**

**Homework 4**

**Lecture 25: Mid-term Exam**

**Lecture 26: Solar cell-Materials (I)**

**Lecture 27: Solar cell-Materials (II)**

**Lecture 28: Materials Deposition: PVD**

**Lecture 29: Materials Deposition: CVD (I)**

**Lecture 30: Materials Deposition: CVD (II)**

**Lecture 31: Transparent Conductive Oxide**

# About MSE 460

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## MOSFETs

**Lecture 32: Electrostatics of MOS Capacitor**

**Lecture 33: C-V Characteristics of MOS Capacitor**

**Lecture 34: Operation of MOSFET**

**Lecture 35: Subthreshold Region of MOSFET And Device Scaling**

**Lecture 36: Velocity Saturation**

**Lecture 37: Short channel effects**

**Lecture 38: Non-ideal semiconductor-gate dielectric interface**

**Lecture 39: High-k/metal gate**

**Lecture 40: 3D Channel and New Channel Materials for MOSFETs**

**Lecture 41: Fabrication Flow of Si MOSFETs**

**Lecture 42: Electrodeposition**

# Grading

Grading will be composed of three elements

1) Homework (6x3%=18%)

6 homework in total.

Collaboration policy: Limited homework collaboration

Homework will be due after the end of the next week, late homework will not be accepted.

2) Exams (2 exams for 82%)

Mid-term exam: 36%

Final exam: 46%

Exams will be open note (1 page, single-sided letter sheet)

Topics covered in mid-term will not be specifically tested in final



# Course Webpage

Website: MSE460.matse.Illinois.edu

**I** ILLINOIS ENGINEERING

## MSE 460: Electronic Materials, Devices, and Processing

Materials Science & Engineering

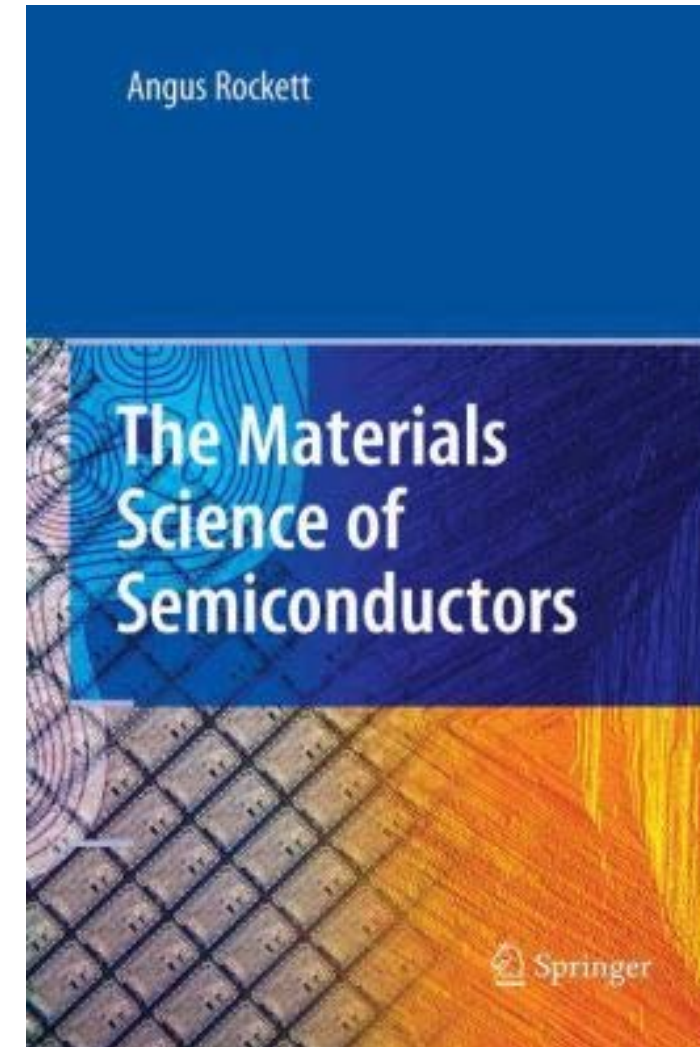
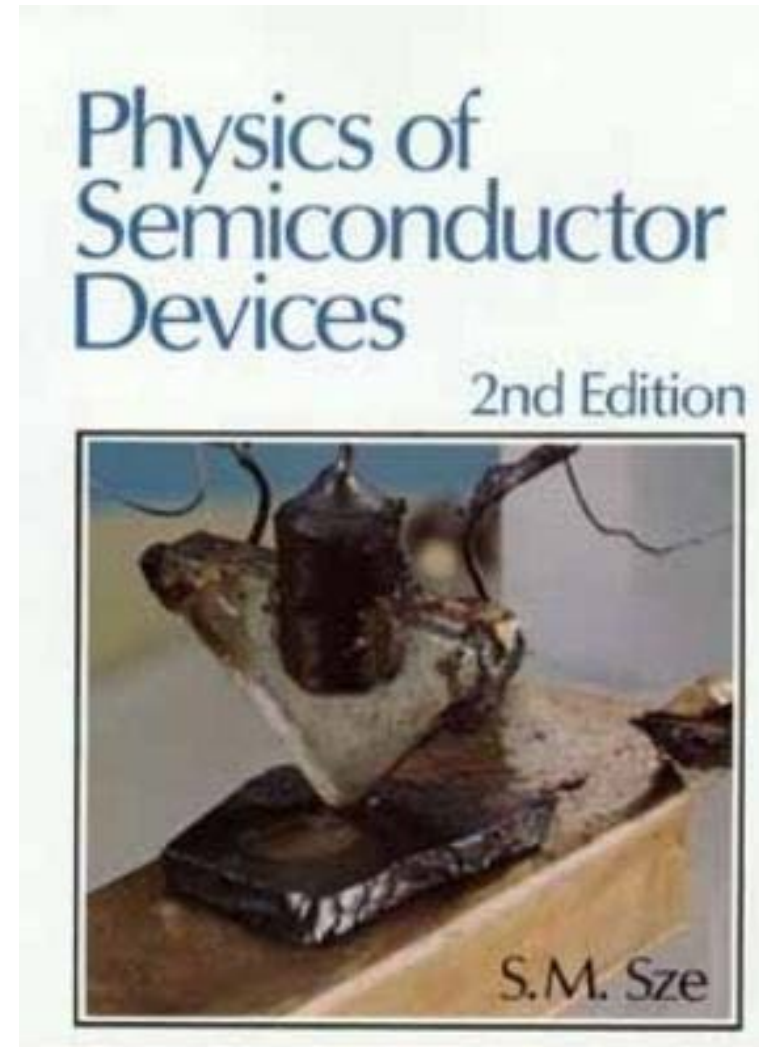
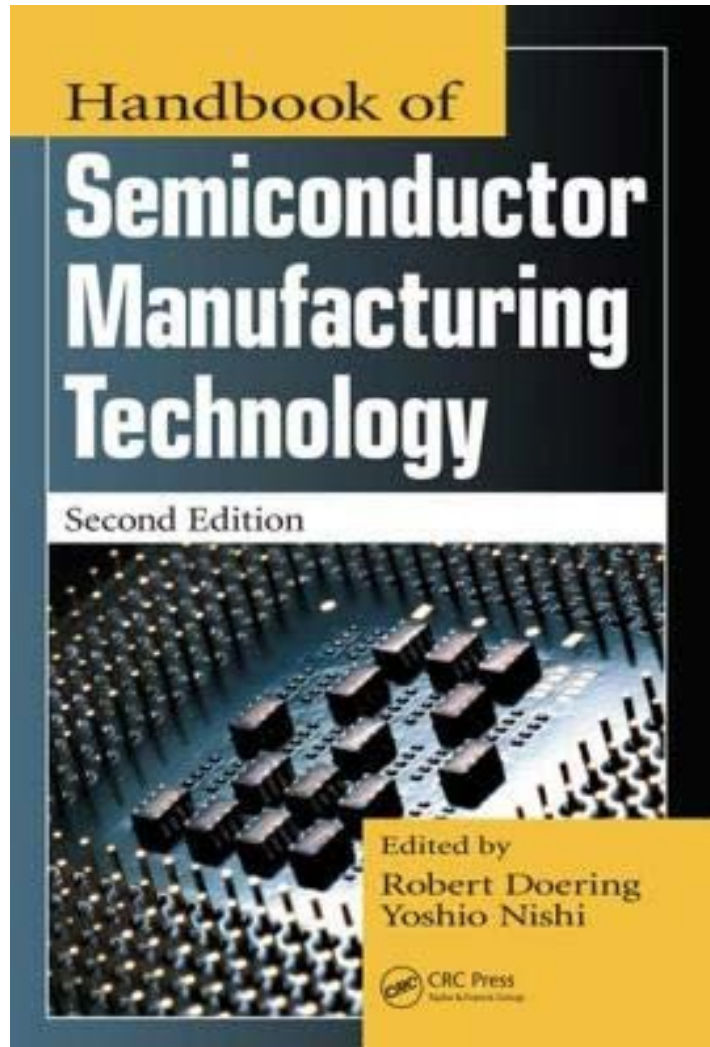
[Home](#) [Syllabus](#) [Lecture Notes](#) [Homework](#) [Exams](#)

## Home

**Welcome to the homepage of Class MSE 460.**

**Course Description:** This class introduces students to materials used in modern electronic and optoelectronic devices. The progress of microelectronic industry is largely driven by the development and introduction of new materials. The structure, chemistry, and processing of materials are closely related to their electronic and optical properties and therefore the device characteristics. This course will cover the processing of electronic materials, the materials science and engineering of semiconductors, the physics behind the operations of various electronic and optoelectronic devices, and the adoption of different materials as well as bulk and nanoscale semiconductor processing techniques to deliver the desired device performances.

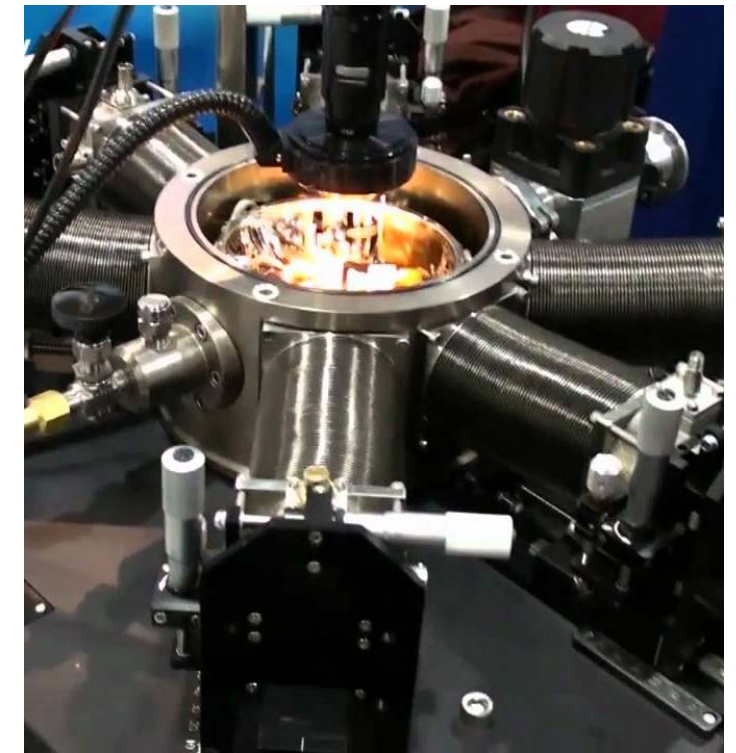
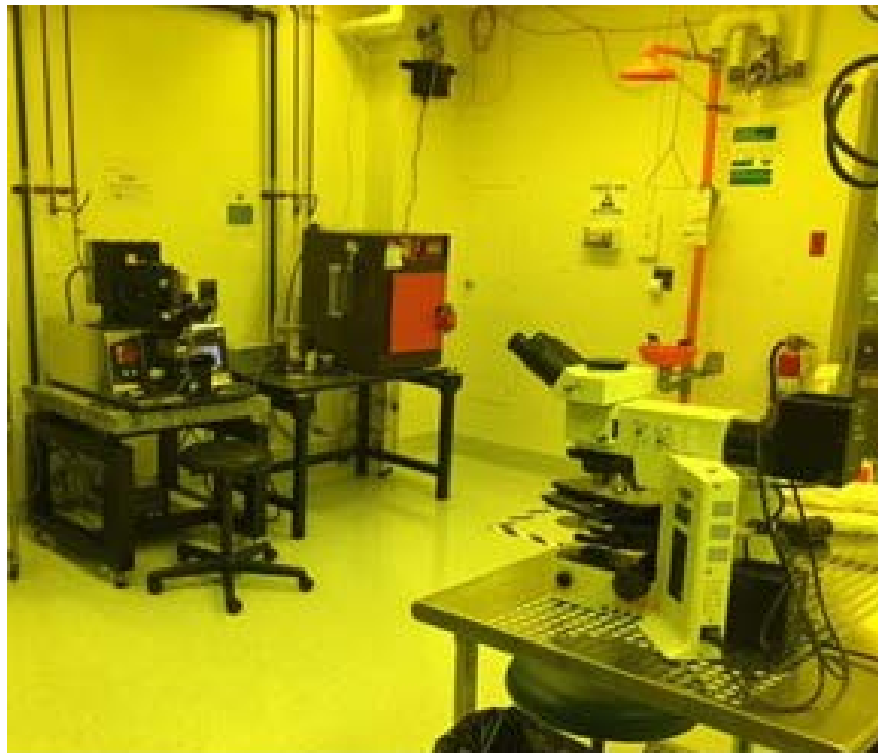
# Textbooks





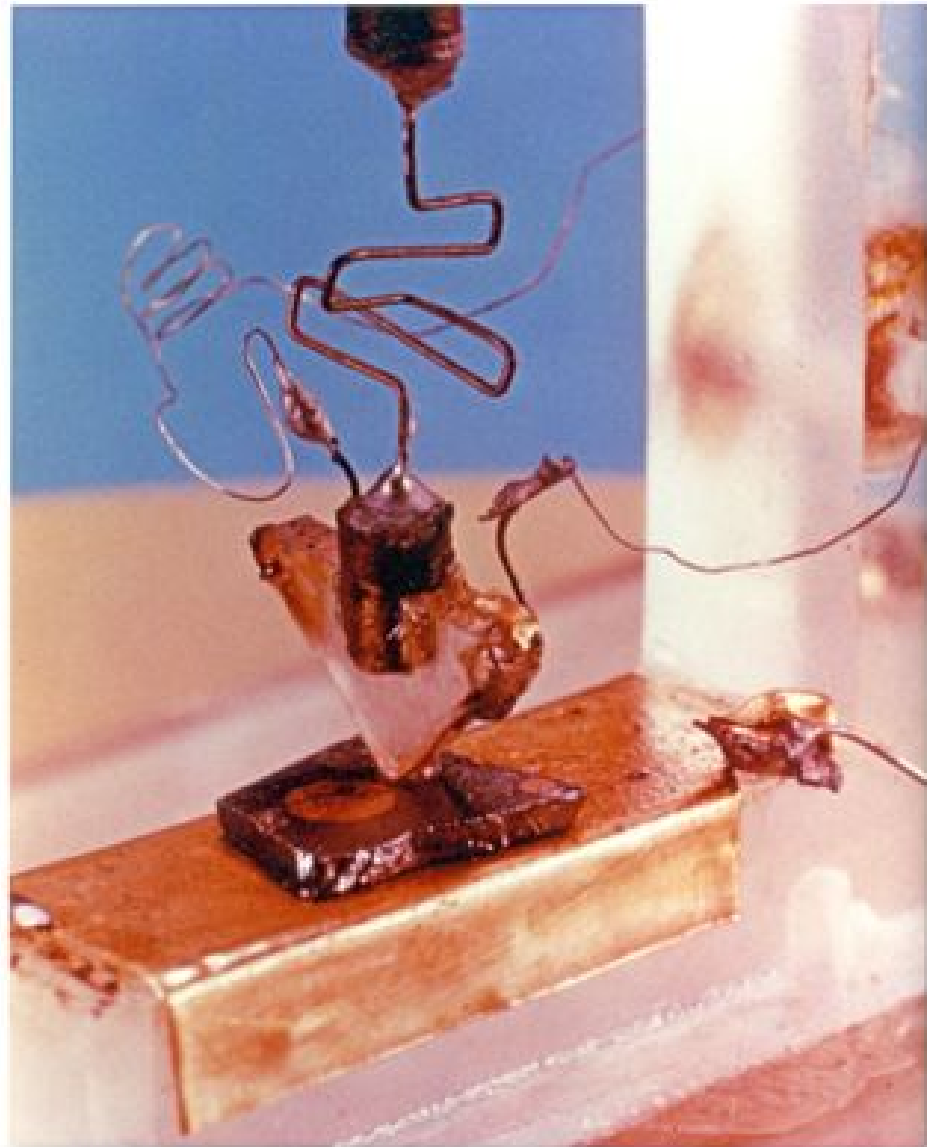
# Advertisement

If you are interested in obtaining hands-on experiences in electronic materials research, you are welcome to discuss with me about the opportunities of research assistants in my group!



Email: [qingcao2@illinois.edu](mailto:qingcao2@illinois.edu)

# First Transistor



John Bardeen

Walter Brattain



William Shockley



# Your Motivations

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## For undergraduate students:

- 1) Overall understanding of the field of electronic materials and electronic devices, and make informed choices if you would like to go to graduate school.
- 2) Scientific knowledge of cutting edge electronics, which will make you distinct if you would like to find a job in either consulting firms or work in the public policy.

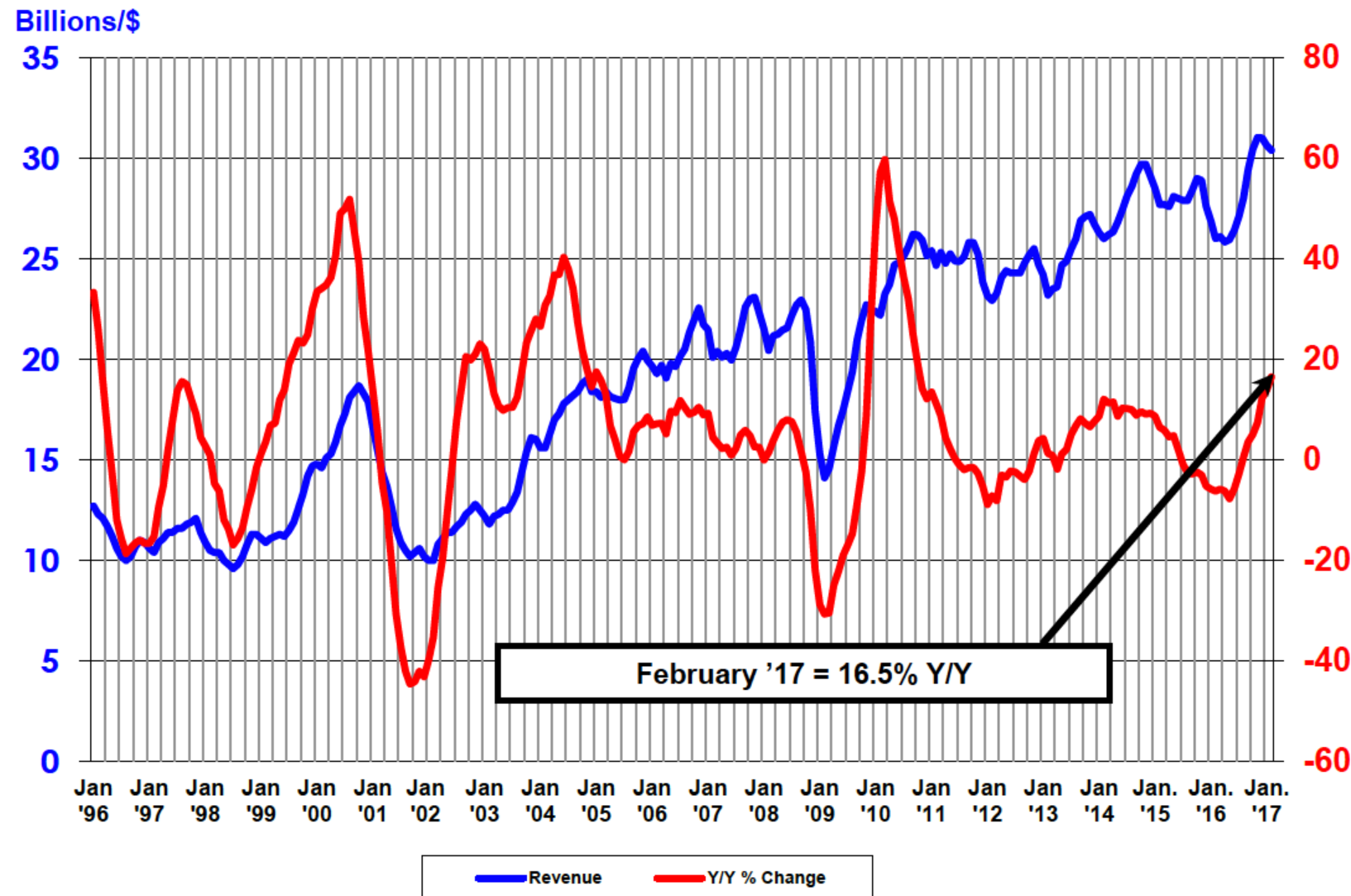
## For graduate students:

- 1) Pass the qualify exam on electronic materials
- 2) Help you to kick start your research: know the concepts, appreciate the problems, understand literatures, be able to communicate with you colleagues including your advisor.

# Overview of Semiconductor Industry

## Worldwide Semiconductor Revenues

Year-to-Year Percent Change



Attributes of the semiconductor industry:

- 1) High capital investment:  
Intel fab 42 at Arizona: 7B  
GF fab 8 at Malta: 8.5B
- 2) High R&D investment:  
Around 20% of total revenue
- 3) High profit margin:  
Industry average gross margin about 60%

# Players/Job Opportunities in Semiconductor Industry

## Integrated Design and Manufacture (IDM)

Logic:

Intel, Samsung

Analog:

TI, Analog Devices, ST  
NXP-Freescale

Memory:

Micron, Hynix

## Fabless

IBM, AMD

Qualcomm, Broadcom

Nvidia

MediaTek

## Foundry

TSMC

UMC

Global Foundry

## Tool

Applied Materials

ASML

Lam Research

Novellus

Varian

# Progress in Electronics

## Computation



1956 IBM SAGE computer:  
1MW  
13,000 transistors, vacuum tubes, and diodes.



2016 Qualcomm Snapdragon 835:  
~1W  
3B transistors.

## Memory



1980  
IBM 3380  
20GB  
4400lbs  
Cost: ~\$0.8M

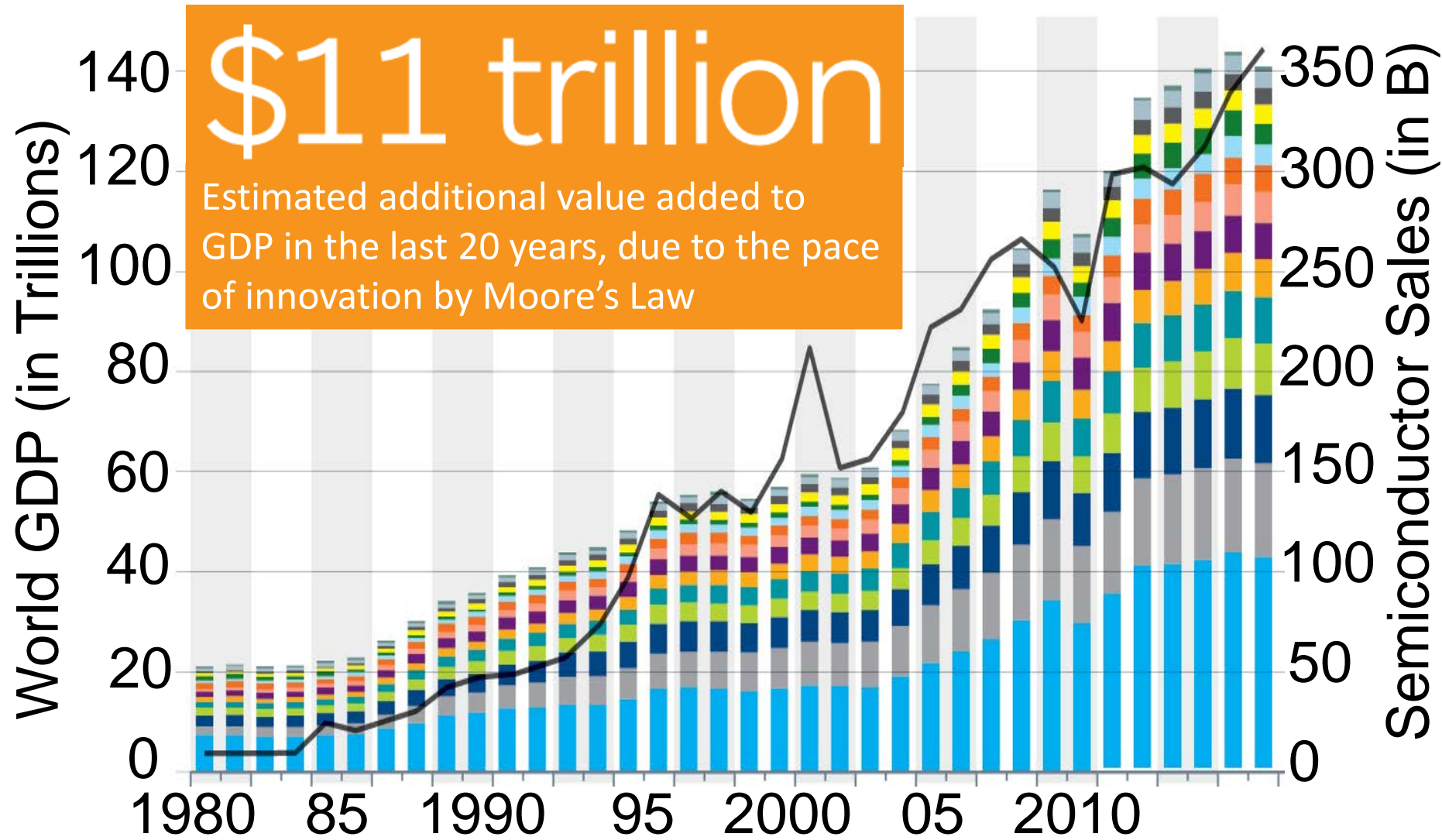


2014  
Sandisk  
512 GB  
0.001lbs  
Cost: ~\$200

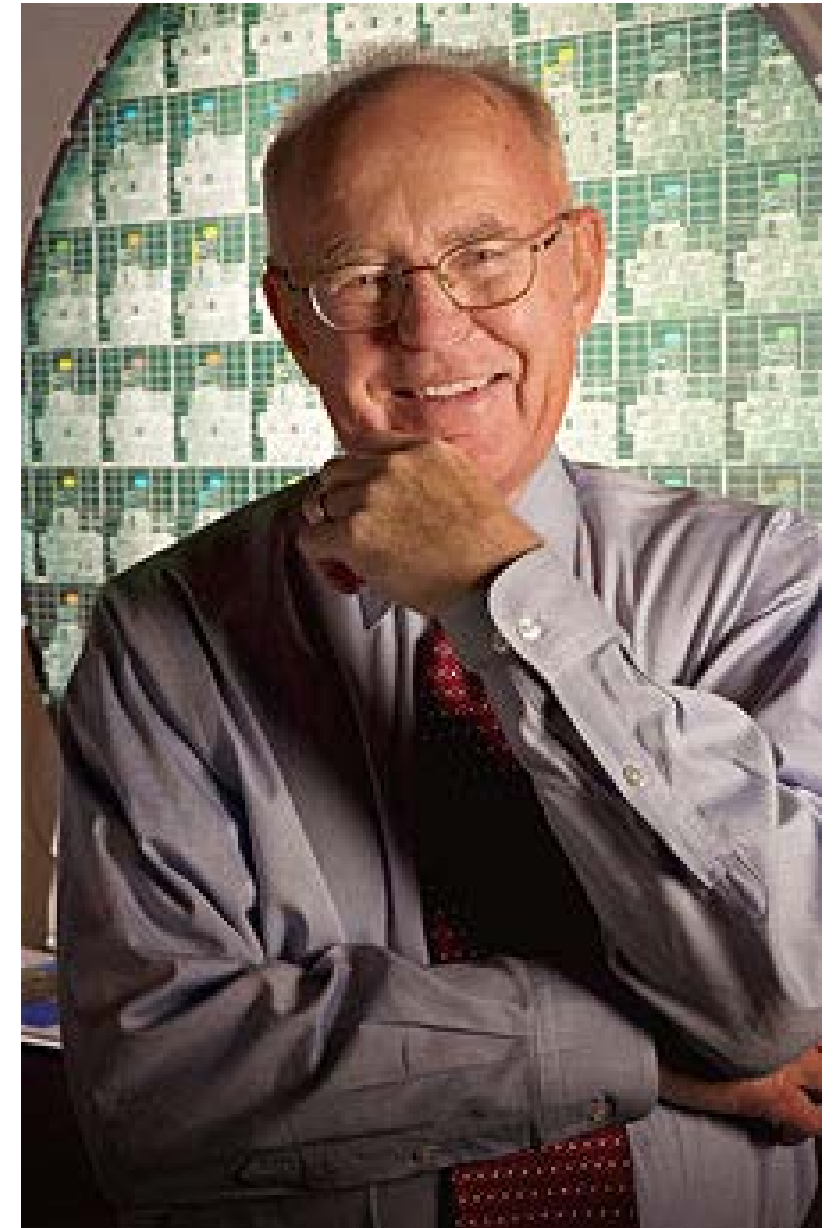
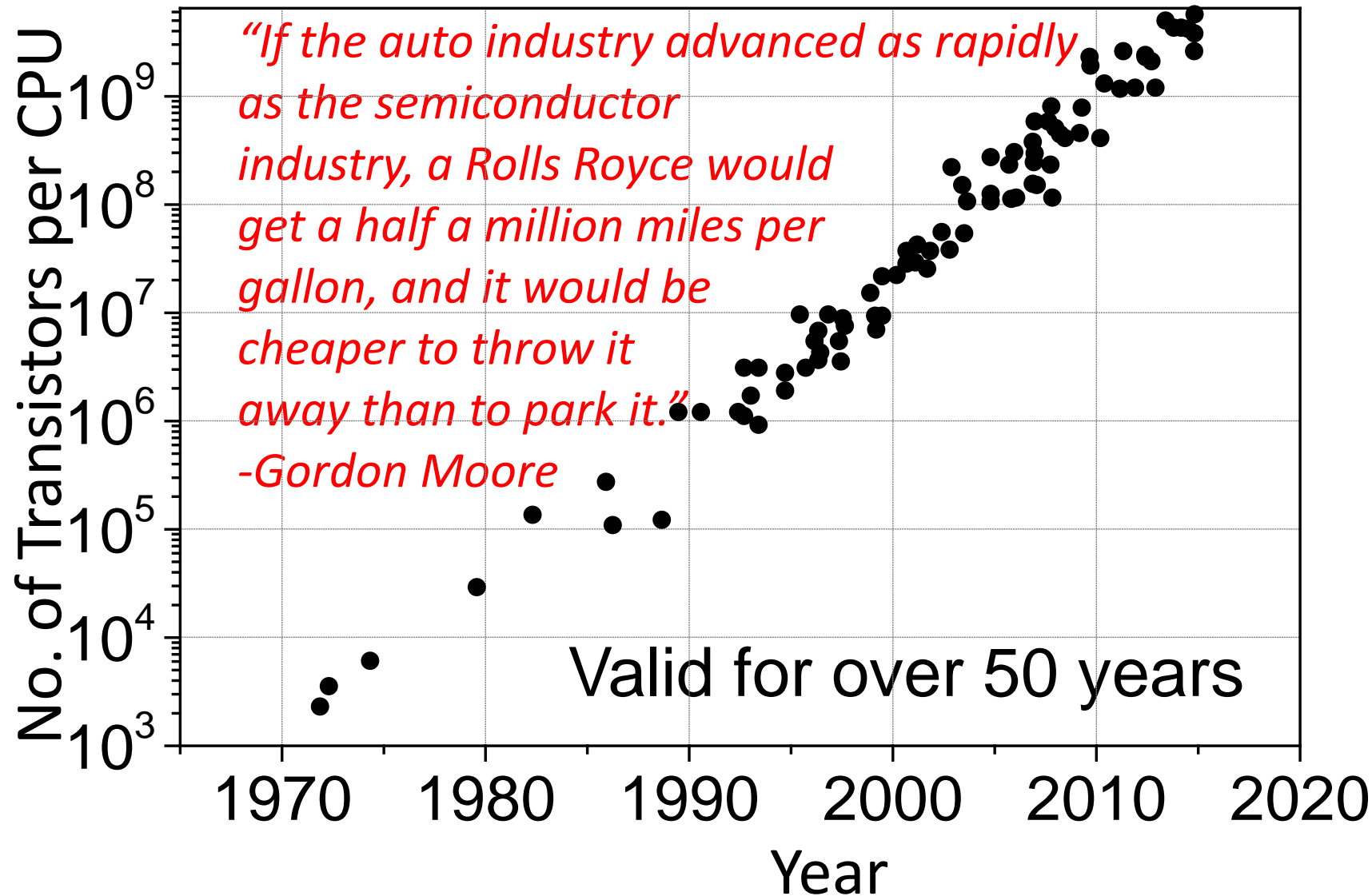




# Economic Impact

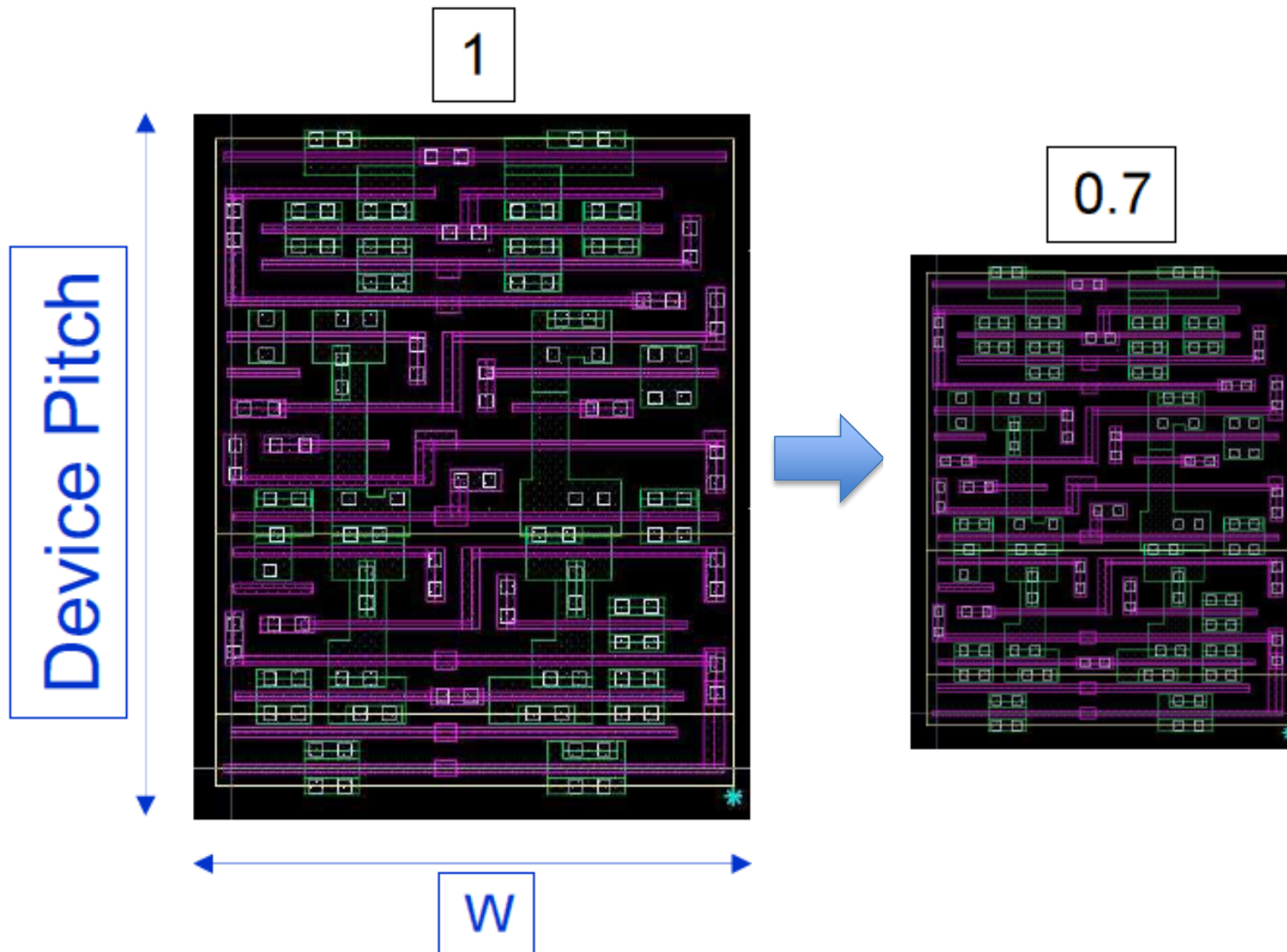


# Greatest Evolutionary Technological Progress



# Fundamental Driving Forces for Semiconductor Industry

## Scaling (Moore's Law)



About every two years:

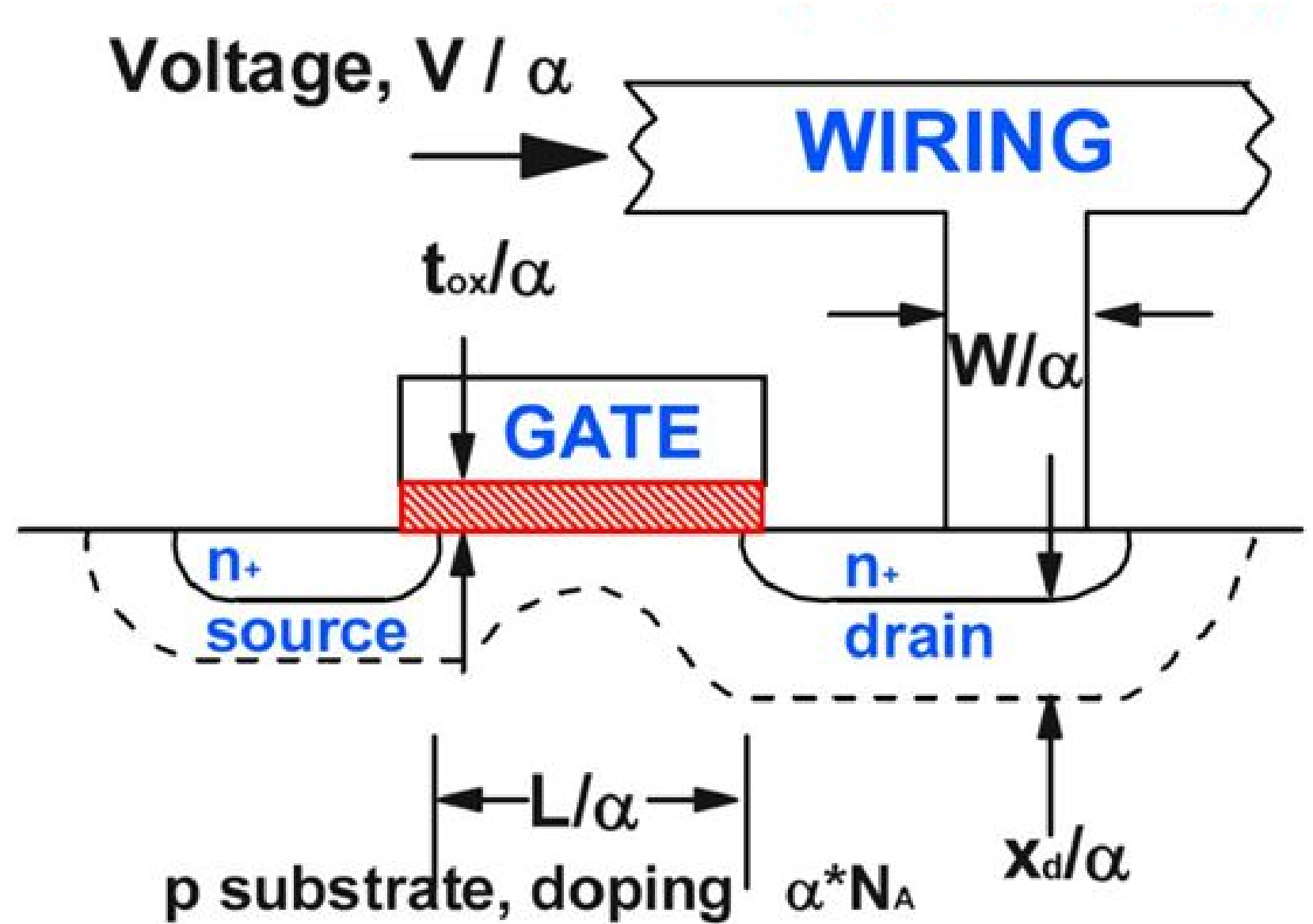
**30% Reduction in  $W$  and device pitch**

- 50% area reduction (**Cost**)

- 2X increase in device/area

**30% drop in power/operation**

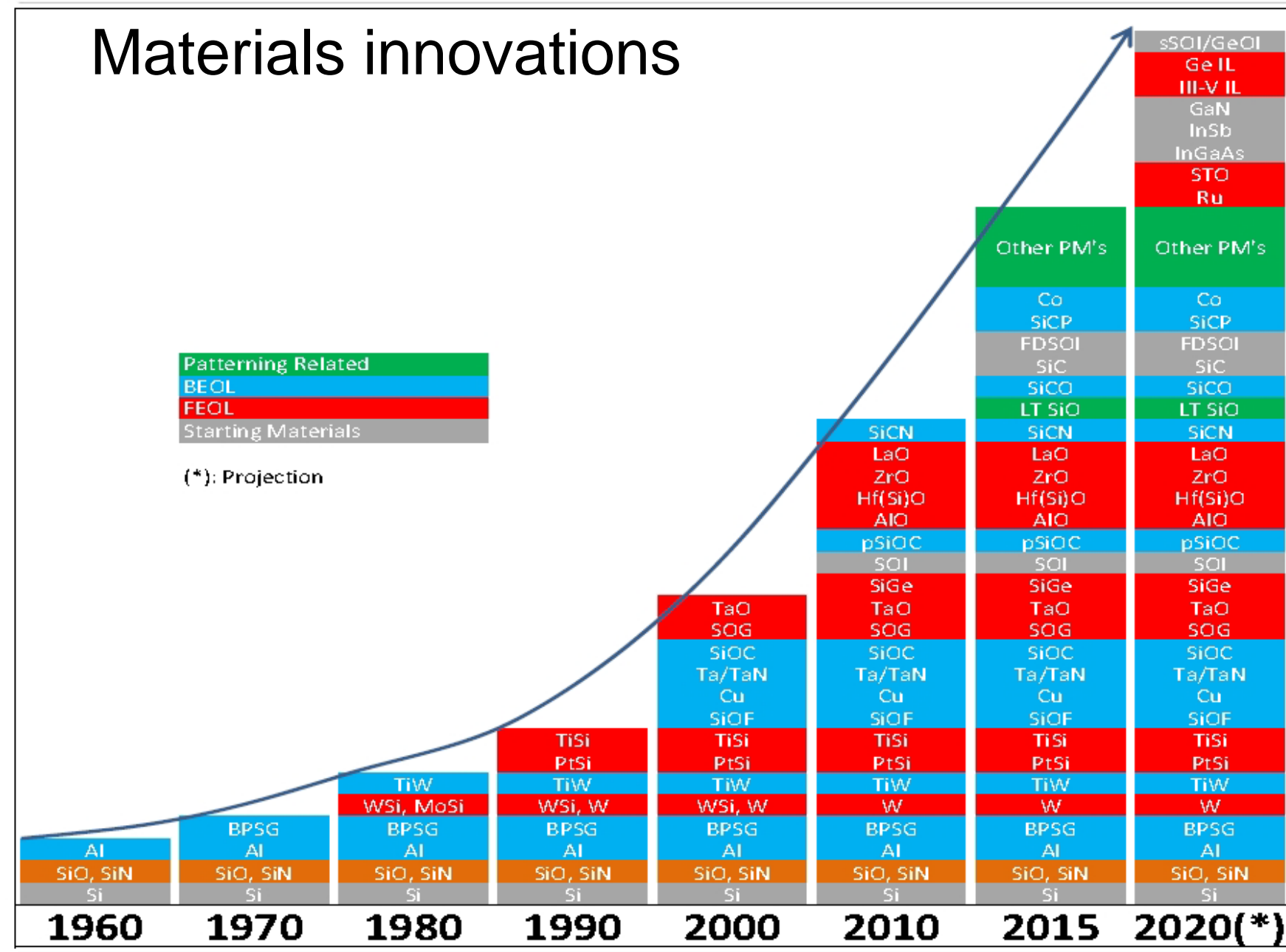
# Dennard Theory





# Fundamental Driving Forces for Semiconductor Industry

## Materials innovations



From the 1960s through the 1990s, only a handful of materials were used, most notably silicon, silicon oxide, silicon nitride and aluminum. Soon, by 2020, more than 40 different materials will be in high-volume production, including more “exotic” materials such as hafnium, ruthenium, zirconium, strontium, et. al.

# As A MatSE Class We Will Cover

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New patterning materials: EUV resist, di-block copolymers

New materials processing: transfer printing, additive manufacturing

New materials for LEDs and solar cells:

organics, quantum dots, CdTe, CIGS, perovskite, et. al.

New materials for transistors:

III-Vs, high k/metal gates, nanotubes, graphenes, 2D TMDCs, et. al.

New materials for memory:

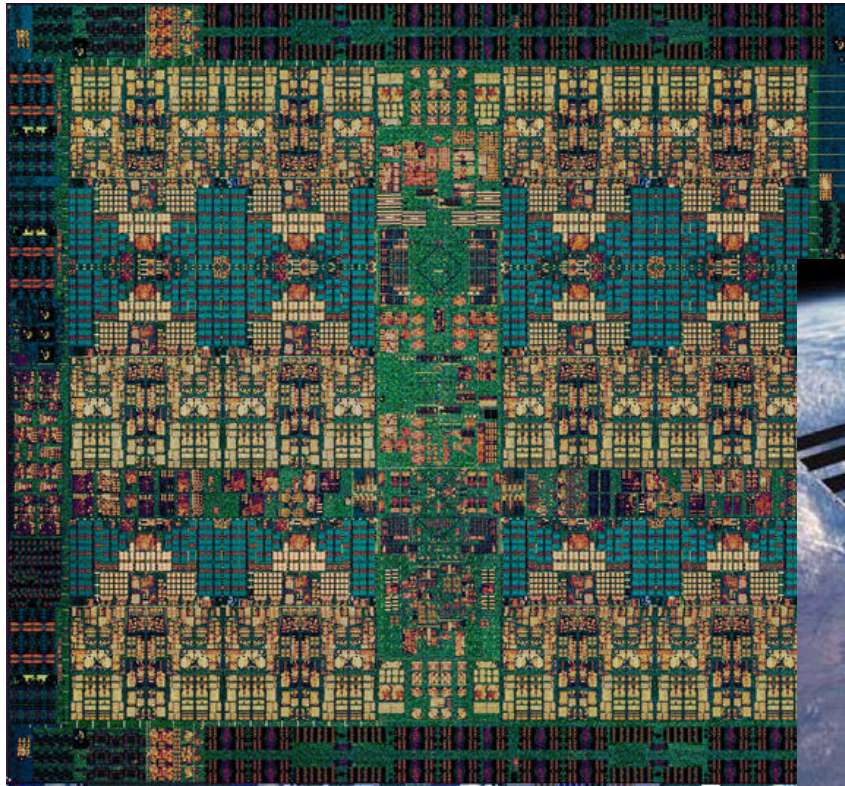
PCM, oxides/chalcogenides for memristors



# Technology Today

IBM Power 9

24 cores with 8B transistors



Multi-junction solar cell  
Efficiency >50%



IBM Flash System  
57TB per building block

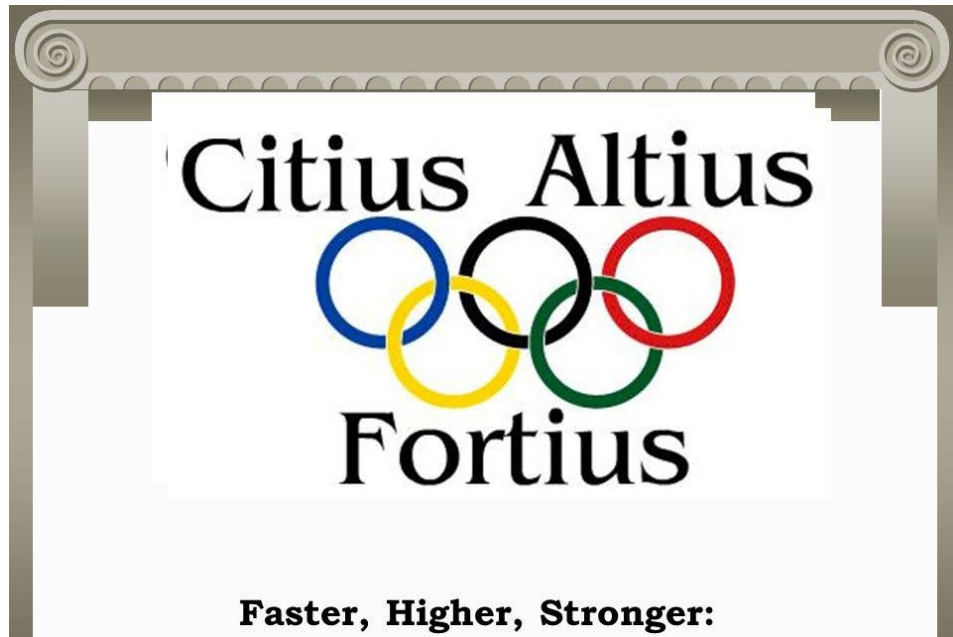




# Challenges Ahead for Our (Your) Generation

- Devices for new paradigms of computing
- More-Moore platform for mobile computing and IoT
- Technologies for Datacenters
- Heterogenous integration for low power and multifunctional system-on-chip
- Better solar cells for renewable energy in TW regime

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**Key enabler: New Electronic Materials**

- More functionality**
- Better performance**
- Lower cost**

# Summary

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1. Logistics about MSE 460
2. Overview of semiconductor industry
3. Fundamental driving forces for semiconductor industry: Physical scaling and new materials
4. Current status and challenges for our (your) generation

**Any Questions/Comments/Suggestions?**